

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	338	703/13.ccor.	US-PGPUB; USPAT	OR	ON	2006/02/02 17:35
S2	548	703/14.ccor.	US-PGPUB; USPAT	OR	ON	2006/02/02 17:35
S3	186	703/15.ccor.	US-PGPUB; USPAT	OR	ON	2006/02/02 17:35
S4	83	703/16.ccor.	US-PGPUB; USPAT	OR	ON	2006/02/02 17:36
S5	106	703/17.ccor.	US-PGPUB; USPAT	OR	ON	2006/02/02 17:36
S6	5	("5754826" or ("5923567") or ("6197605") or ("6768983") or ("6891626")).PN.	US-PGPUB; USPAT	OR	OFF	2006/02/02 17:43
S7	24	optical adj digital adj profil\$	US-PGPUB; USPAT	OR	ON	2006/02/02 17:43
S8	4	S7 and @ad<="20020228"	US-PGPUB; USPAT	OR	ON	2006/02/02 17:43
S9	70	Specular adj Spectroscopic adj Scatterometry	US-PGPUB; USPAT	OR	ON	2006/02/02 17:46
S10	31	S9 and @ad<="20020228"	US-PGPUB; USPAT	OR	ON	2006/02/02 17:47
S11	37586	(integrated adj circuit) and simulat\$4	US-PGPUB; USPAT	OR	ON	2006/02/02 17:47
S12	7010	S11 and profil\$	US-PGPUB; USPAT	OR	ON	2006/02/02 17:47
S13	489	S12 and metrology	US-PGPUB; USPAT	OR	ON	2006/02/02 17:48
S14	408	S13 and fabricat\$4	US-PGPUB; USPAT	OR	ON	2006/02/02 17:48
S15	75	S14 and attribute	US-PGPUB; USPAT	OR	ON	2006/02/02 17:48
S16	24	S15 and @ad<="20020228"	US-PGPUB; USPAT	OR	ON	2006/02/02 17:49
S17	13791	critical adj dimension	US-PGPUB; USPAT	OR	ON	2006/02/02 17:49
S18	6844	S17 and shape	US-PGPUB; USPAT	OR	ON	2006/02/02 17:50
S19	38	S15 and S18	US-PGPUB; USPAT	OR	ON	2006/02/02 17:53
S20	5	S19 and @ad<="20020228"	US-PGPUB; USPAT	OR	ON	2006/02/02 18:02
S21	5	("4342090" "4949275" "5313398" "5355320" "5379237").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/02 19:08
S22	71	("5539652").URPN.	USPAT	OR	ON	2006/02/02 19:23

		Results
13.	(((((pub-date > 1959 and pub-date < 2003 and FULL-TEXT(simulat!) and FULL-TEXT(metrology)) and integrated circuit) and profile) and parameter) and device) and circuit) and amplifier [All Sources(- All Sciences -)]	7
12.	(((((pub-date > 1959 and pub-date < 2003 and FULL-TEXT(simulat!) and FULL-TEXT(metrology)) and integrated circuit) and profile) and parameter) and device) and circuit) and interconnect [All Sources(- All Sciences -)]	7
11.	(((((pub-date > 1959 and pub-date < 2003 and FULL-TEXT(simulat!) and FULL-TEXT(metrology)) and integrated circuit) and profile) and parameter) and device) and circuit [All Sources(- All Sciences -)]	40
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9.	((((pub-date > 1959 and pub-date < 2003 and FULL-TEXT(simulat!) and FULL-TEXT(metrology)) and integrated circuit) and profile) and parameter) and attribute [All Sources(- All Sciences -)]	5
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4.	((((pub-date > 1959 and pub-date < 2003 and FULL-TEXT(simulat!) and FULL-TEXT(critical dimension)) and profile) and parameter) and attribute [All Sources(- All Sciences -)]	21
3.	((pub-date > 1959 and pub-date < 2003 and FULL-TEXT(simulat!) and FULL-TEXT(critical dimension)) and profile) and parameter [All Sources(- All Sciences -)]	255
2.	((pub-date > 1959 and pub-date < 2003 and FULL-TEXT(simulat!) and FULL-TEXT(critical dimension)) and profile [All Sources(- All Sciences -)]	318
1.	pub-date > 1959 and pub-date < 2003 and FULL-TEXT(simulat!) and FULL-TEXT(critical dimension) [All Sources(- All Sciences -)]	1059

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#1	((integrated circuit<and>simulat*)<and>profile) <and> (pyr >= 1951 <and> pyr <= 2002)	5977
#2	((attribute<and>metrology)<and>parameter) <and> (pyr >= 1951 <and> pyr <= 2002)	376
#3	((((integrated circuit<and>simulat*)<and>profile) <and> (pyr >= 1951 <and> pyr <= 2002)) <AND> (((attribute<and>metrology) <and>parameter) <and> (pyr >= 1951 <and> pyr <= 2002)))	42
#4	((fabrication<and>critical dimension)<and>shape) <and> (pyr >= 1951 <and> pyr <= 2002)	182
#5	(((((integrated circuit<and>simulat*)<and>profile) <and> (pyr >= 1951 <and> pyr <= 2002)) <AND> (((attribute<and>metrology) <and>parameter) <and> (pyr >= 1951 <and> pyr <= 2002))) <AND> (((fabrication<and>critical dimension)<and>shape) <and> (pyr >= 1951 <and> pyr <= 2002)))	5

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1 Substrate modeling and lumped substrate resistance extraction for CMOS ESD/latchup circuit simulation



Tong Li, Ching-Han Tsai, Elyse Rosenbaum, Sung-Mo Kang

June 1999

Proceedings of the 36th ACM/IEEE conference on Design automation

Publisher: ACM Press

Full text available: pdf(848.82 KB)

Additional Information: [full citation](#), [references](#), [index terms](#)

2 Analysis and optimization of thermal issues in high-performance VLSI



Kaustav Banerjee, Massoud Pedram, Amir H. Ajami

April 2001

Proceedings of the 2001 international symposium on Physical design

Publisher: ACM Press

Full text available: pdf(320.70 KB)

Additional Information: [full citation](#), [abstract](#), [references](#), [citations](#), [index terms](#)

3 Your core— my problem? (panel session): integration and verification of IP



Gabe Moretti, Tom Anderson, Janick Bergeron, Ashish Dixit, Peter Flake, Tim Hopes, Ramesh Narayanaswamy

June 2001

Proceedings of the 38th conference on Design automation

Publisher: ACM Press

Full text available: pdf(129.32 KB)

Additional Information: [full citation](#), [abstract](#), [index terms](#)

4 Graphic applications to aerospace structural design problems



A. L. Eshleman, H. D. Meriwether

January 1987

Proceedings of the 4th conference on Design automation

Publisher: ACM Press

Full text available: pdf(1.55 MB)

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5 Survey of image quality measurements



Ikram E. Abdou, Nicolas J. Dusaussay

November 1986 **Proceedings of 1986 ACM Fall joint computer conference**

Publisher: IEEE Computer Society Press

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and program complex, high-speed, digital **integrated circuits** within their own work environments.

1 A **Simulation Tool For Dynamically Reconfigurable Field**
also require less external memory for storage. The **profile** of the circuitry that is active on the array
dr14.eee.strath.ac.uk/papers/pl_ieee96.ps.Z

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realization of densely packed (mixed signal) **integrated circuits** is prevention of cross-talk via the
and currents in the substrate, either by **simulation** of a 3D resistance mesh of the complete
The resistivity varies, because of the doping **profile**, only in the direction perpendicular to the
donau.et.tudelft.nl/pub/space/doc/1995/iccad95.ps.Z

[Simulation-based Performance Analysis of Distributed Systems - Schwarz, al. \(1997\) \(Correct\) \(3 citations\)](#)
Ulrich Donath Fraunhofer-Institute for **Integrated Circuits** Design Automation Department Zeunerstrasse
time-consuming method is the construction of a **simulation** model which includes the different subsystems,
subsystems, the communication system, and the load **profile**. In particular, this approach seems to be very
www.eas.iis.fhg.de/sim/publications/papers/1997/006/paper.ps.gz

[REDO - Random Excitation and Deterministic.. - Grimalia, Lee.. \(1999\) \(Correct\) \(2 citations\)](#)
term defects to denote actual flaws in an **integrated circuit**, which introduce erroneous operation for
ATPG process [FERG91]In this case, the fault **simulation** engine is modified to allow the **simulation** of
process. Specifically, each site's fault detection **profile** is lost in modern fault simulators because they
dropzone.tamu.edu/techpubs./1999/ece9902.ps.gz

[Finite Element Resolution Of The 3d Stationary.. - Pena, Bruguera, Zapata \(1997\) \(Correct\) \(1 citation\)](#)
devices is an essential tool for **integrated circuit** designers. These simulators lead to an
mapping problem. 1 Introduction The numerical **simulation** of semiconductor devices is an essential tool
electron and hole concentrations and the doping **profile**, and R is the recombination-generation rate.
ftp.ac.uma.es/pub/reports/1997/UMA-DAC-97-01.ps.gz

[Efficient Electrostatic and Electromagnetic Simulation Using.. - Kapur, Long \(Correct\)](#)
are often used to extract models of **integrated circuit** structures. This extraction involves
Efficient Electrostatic and Electromagnetic Simulation Using IES 3 Sharad Kapur David E. Long Bell
material variations (e.g.the doping **profile** of a MOSFET)the differential approach is
www.bell-labs.com/user/kapur/Papers/ieee98.ps.gz

[PARTICS: A PARallel Taskfarm for Integrated Circuit.. - Gaston, Alexander.. \(Correct\)](#)
PARTICS :A PARallel Taskfarm for **Integrated Circuit** Simulators G.J. Gaston, W.J.C. Alexander,
for performing CPU intensive process and device **simulations**. The system gives an almost linear speed up is
more CPU intensive. The structure and doping **profile** calculated by process **simulation**, provide
ftp.epcc.ed.ac.uk/pub/tr/91/tr9108.ps.Z

[Modeling And Simulation Of High Speed Interconnects - Biswas \(1998\) \(Correct\)](#)
Chapter 1 Introduction 1.1 Motivation As **integrated circuit** processing technology marches relentlessly
Modeling And **Simulation** Of High Speed Interconnects By Baribrata
CMOS Inverter. 10 3.3 Vertical **Profile** of a two layer metal and a single layer poly
www.i3s.leeds.ac.uk/homes/MBS/vitae_theses/biswas_ms_1998.pdf

[Compact Model Specification of RF MOSFET with DC and AC Evaluations - Kolding \(1999\) \(Correct\)](#)
to fully exploit the flexibility inherent to **integrated circuit** design. Most CMOS manufacturing facilities
MOSFET layout can be used to give better **simulation** results by including layoutdependent
transistor into inversion [30]Hence, the doping **profile** of the well changes with depth making analysis
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